Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	951	327/105	US-PGPUB; USPAT; USOCR	AND	ON	2007/06/10 21:01
L3	77	L2 and (current adj mirror)	US-PGPUB; USPAT; USOCR -	AND	ON	2007/06/10 21:01
L4	3708	((driving adj circuit\$3 near display) or (current adj driver near display))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/06/10 21:03
L5	14	L4 and (MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/06/10 21:04
L6	77	L2 and (current adj mirror)	US-PGPUB; USPAT; USOCR	AND	ON	2007/06/10 21:11
L7	29	L6 and (IC or (semiconductor adj chip))	US-PGPUB; USPAT; USOCR	AND .	ON	2007/06/10 21:11
L8	2976	327/538	US-PGPUB; USPAT; USOCR	AND	ON	2007/06/10 21:13
L9	6	L8 and (MISFET)	US-PGPUB; USPAT; USOCR	AND	ON	2007/06/10 21:13
L10	. 6	L8 and (MISFET)	US-PGPUB; USPAT; USOCR	AND	ON	2007/06/10 21:13
L11	1041	MISFET same MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2007/06/10 21:14
L12	132	L11 and display	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2007/06/10 21:14
L13	77	L12 and chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2007/06/10 21:15

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L14	3708	((driving adj circuit\$3 near display) or (current adj driver near display))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/06/10 21:17
L15	41	L14 and (semiconductor near chip)	US-PGPUB; USPAT; 'EPO; JPO; DERWENT; IBM_TDB	AND	ON.	2007/06/10 21:17
L16	30	L15 NOT Date	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/06/10 21:17
L17	7	L16 and (current with (mirror or source or reference))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/06/10 21:17
L18	0	L17 and (MISFET or MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/06/10 21:17
L19	0	(current driving device semiconductor chip first-conductive-type first MISFET reference current source reference current flow first-conductive-type current distribution MISFET current mirror circuit first MISFET and makes the reference second-conductive-type current input MISFET current distribution MISFET current supply sections source MISFETs current mirror). CLM.	US-PGPUB	AND	ON	2007/06/10 21:17
L20	0	(current driving device semiconductor chip first-conductive-type MISFET current source reference conductive-type current distribution MISFET second-conductive-type current input MISFET current distribution MISFET current supply sections source MISFETs).CLM.	US-PGPUB	AND	ON	2007/06/10 21:18

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S1	2	"6,332,661".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 18:05
S2	2812	323/315	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND .	ON	2006/04/27 15:03
<b>S3</b>	8	S2 and MISFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:37
S4		S3 and reference adj current	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:04
S5	2	US "20040227499"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/30 19:23
S6		S3 and (current adj reference)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND .	ON	2006/04/27 15:38
<b>S</b> 7	4	S3 and (mirror)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:38
S8	. 3	S7 and (semiconductor near chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:12
S10	2	S8 and (display or (display with data))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:43
S11	3	S3 and (display or (display with data))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:45

S12	1	S2 and ((driving adj circuit\$3 near display) or (current adj driver near display))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:50
S13	0	S12 and "200"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON .	2006/04/27 15:47
S14	4	S3 and "200"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:47
S15	. 0	S3 and ("200" near meter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:47
S16	3234	((driving adj circuit\$3 near display) or (current adj driver near display))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:11
S17	10	S16 and (MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/06/10 21:03
S18	8	S17 and reference	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:50
S19	5	S18 and mirror	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 15:51
S20	1	S19 and "200"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 16:39
S21	542 ·	327/53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND .	ON	2006/04/27 16:40

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S22	2	S21 and (MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND .	ON .	2006/04/27 16:49
S23	537	327/66	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 16:49
S25	3	S23 and (MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 16:50
S26	9	("3365584"   "4825104"   "4912745"   "5004932"   "5469392").PN. OR ("5838166"). URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/27 16:54
S27	841	327/105	US-PGPUB; USPAT; USOCR	AND	ΟN	2006/04/27 16:55
S28	3	S27 and (MISFET)	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/27 16:56
S29	68	S27 and (current adj mirror)	US-PGPUB; USPAT; USOCR	AND	ON .	2007/06/10 21:01
S30	189	S27 and (IC or (semiconductor adj chip))	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/27 16:57
S31	26	S29 and (IC or (semiconductor adj chip))	US-PGPUB; USPAT; USOCR	AND	ON	2007/06/10 21:11
S32	2657	327/538	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/27 17:46
S33	6	S32 and (MISFET)	US-PGPUB; USPAT; USOCR	AND	ON	2007/06/10 21:13
S34	748	327/539	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 17:49

S35	1	S34 and (MISFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 17:50
S36	1754	327/540	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 17:50
S37	0	S36 and (MISFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND .	ON ·	2006/04/27 17:51
S38	1685	327/541	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND .	ON	2006/04/27 17:51
S39	. 5	S38 and (MISFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 17:53
S40	308	327/542	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 17:53
S41	0	S40 and (MISFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON .	2006/04/27 17:53
S42	1777	327/543	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 17:53

S43	3	S42 and MISFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 17:54
S44	15	("4195356"   "5199000").PN. OR ("5392243").URPN.	US-PGPUB; USPAT; USOCR	AND	ON .	2006/04/27 17:55
S45	3	"20030151567"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:16
S46	. 3	"20030151567"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 18:08
S47	. 2	"20030122808"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/27 18:08
S48		"20030151567"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 15:07
S49	4	("6586888"   "6747417"   "6756738"   "6777885").PN. OR ("6992647").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/28 15:07
S50	3862	315/169.3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:16
S51	1	S50 and (MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:17
S52	2005	315/169.4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:17

S53	1	S52 and (MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:17
S54	30	("3725899"   "4432610"   "5349366"   "5412596"   "5642213"   "5668754").PN. OR ("6072454"). URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/28 16:19
S55	1456	345/76	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/28 16:19
S56	0	S55 and (MISFET)	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/28 16:19
S57	3584	345/204	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/28 16:19
S58	5	S57 and (MISFET)	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/28 16:19
S59	9	("3862360"   "4532506"   "5200741").PN. OR ("5587722"). URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/28 16:21
S60	0	(current adj driving) near (semiconductor adj chip) near display	US-PGPUB; USPAT; USOCR	AND	ON	2006/04/28 16:22
S61	0	(current adj driving) near (semiconductor adj chip) near display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:22
S62	0	(current near3 driv\$3) near (semiconductor near3 chip) near (display or terminal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND .	ON	2006/04/28 16:23
S63	1	US "20040227499"	US-PGPUB	AND .	ON	2006/04/28 16:24

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S64	0	(current driving device semiconductor chip first-conductive-type first MISFET reference current source reference current flow first-conductive-type current distribution MISFET current mirror circuit first MISFET and makes the reference second-conductive-type current input MISFET current distribution MISFET current supply sections source MISFETs current mirror). CLM.	US-PGPUB	AND	ON	2007/06/10 21:17
S65	0	(current driving device semiconductor chip first-conductive-type MISFET current source reference conductive-type current distribution MISFET second-conductive-type current input MISFET current distribution MISFET current supply sections source MISFETs).CLM.	US-PGPUB	AND	ON	2007/06/10 21:18
S66	1	(current driving device semiconductor chip MISFET current source reference MISFET current input MISFET current distribution MISFET current supply sections source).CLM.	US-PGPUB	AND	ON	2006/04/28 16:29
S67	3	"20030184568"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/08/16 12:27
S71	39	2003/0184568 "6,456,270" "6,509, 854" "6,586,888" "6,765,560" "6, 882,186" "6,897,619" "6,924,601" "6,958,742"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 10:40
S72	6795047	2003/0184568 "6,456,270" "6,509, 854" "6,586,888" "6,765,560" "6, 882,186" "6,897,619" "6,924,601" "6,958,742" "9"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 13:05
S74	0	2003/0184568	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .·	ON	2006/11/14 13:05

S75	2	"US 20040227499"	US-PGPUB; USPAT; USOCR; DERWENT	AND	ON	2006/11/14 15:07
S76	9	62-262517 5-216439 11-205147 11-340765 2000-310981 2002-202823	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 15:12
S77	0	62-262517	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 15:12
S78	1	5-216439	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/11/14 15:13
S79		11-205147	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 15:14
S80	. 3	11-340765	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 15:28
S81	832336	Matsushita.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 15:29
S83	394	S81 and Date.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/11/14 15:31

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584	120	S83 and (display)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 17:15
S93	355	"200.mu.m"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/10 21:00
S94	0.	S84 and S93	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 15:34
S95	591	"\$3.mu.m"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 15:35
S96	0	S84 and S95	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/11/14 15:35
S97	14	S84 and MISFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 16:22
S98	. 21	S84 and chip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 17:47
S99	9	S98 NOT S97	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 16:18

S10 0		S84 and MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 16:22
S10 1		S100 NOT S99	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 16:26
S10 2	27	S84 and (current adj source)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 16:26
S10 3		S102 NOT S101	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/11/14 17:15
S10 4	16	S84 and (display adj driver)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 17:16
S10 5	10	S104 and (chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON .	2006/11/14 17:16
S10 6	8	S105 and (MISFET or MOSFET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/14 17:16
S11 0	1	MOSFET type MISFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/11/16 18:21

S11 1	6	MISFET type MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	OŅ	2006/11/16 18:23
S11 2	986	MISFET same MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/11/16 18:24
S11 3	124	S112 and display	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/11/16 18:24
S11 4	74	S113 and chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2007/06/10 21:14
S11 5	0	S114 and "type of"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON-	2006/11/16 18:24
S11 6	73	S114 and type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/11/16 18:24
S11 7	415	MISFET same MOSFET same type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/11/16 18:24
S11 8	32	S117 and display	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/11/16 18:25
S11 9	12	S118 and chip	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON .	2006/11/16 18:33
S12 0	2	"6924601".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2006/11/16 18:33

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S12 1	· 2	"US 20040227499"	US-PGPUB; USPAT; USOCR; DERWENT	AND	ON	2006/11/16 18:48
S12 2	3	"20050180243"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:02
S12 3	3475	((driving adj circuit\$3 near display) or (current adj driver near display))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:11
S12 4	3475	((driving adj circuit\$3 near display) or (current adj driver near display))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:12
S12 5	127	S124 and (MISFET or MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:12
S12 6	37	S124 and (semiconductor near chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:13
S12 7	. 27	S126 NOT Date	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:14
S12 8	6	S127 and (current with (mirror or source or reference))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:46
S12 9	832362	Matsushita.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:16
S13 0	394	S129 and Date.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:16

S13 1	21	S130 and (display and chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/16 19:16
S13 6	834836	Matsushita.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:38
S13 7	394	S136 and Date.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND .	ON	2006/11/29 16:38
S13 8	21	S137 and (display and chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:38
S13 9	14	S138 and (MOSFET or MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:38
S14 0 ,	3491	((driving adj circuit\$3 near display) or (current adj driver near display))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND .	ON .	2006/11/29 16:46
S14 1	127	S140 and (MISFET or MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:46
S14 2	37	S140 and (semiconductor near chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:47
S14 3	27	S142 NOT Date	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:46
S14 4	6	S143 and (current with (mirror or source or reference))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:46

S14 5	0	S144 AND S141	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 16:46
S14 6	0	S144 and (MISFET or MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/06/10 21:17
S14 7	9	S141 and (semiconductor near chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 18:08
S14 8	1364	((EL or electroluminescent) and (display adj driver))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 19:39
S14 9	75	S148 and (MISFET or MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 19:39
S15 0	55	S149 NOT Date	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 19:39
S15 1	55	S150 not (Matsushita)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/11/29 19:40

S15 5	0	(current driv\$3 semiconductor chip first-conductive-type first MISFET reference current source reference current flow transmitted first-conductive-type current distribution MISFET current mirror second-conductive-type current input MISFET plurality current supply sections second-conductive-type current source MISFETs current mirror circuit current input MISFET output terminal outputting current display data second-conductive-type current transmission MISFET constituting reference current	US-PGPUB	AND	ON	2006/11/30 19:27
		output terminal region semiconductor chip located distance "200" ".mu.m" outputs current transmitted current transmission MISFET).clm.				
S15 6	0	(current driv\$3 semiconductor conductive MISFET reference current source flow transmitt\$3 distribution MISFET current mirror second-conductive-type input MISFET current suppl\$3 current source MISFETs input MISFET output terminal current display data transmission MISFET output terminal distance "200" ".mu.m" output\$3 current transmission MISFET).clm.	US-PGPUB	AND	ON	2006/11/30 19:29
S15 7	0	(current driv\$3 semiconductor MISFET reference source flow transmitt\$3 distribution current mirror second-conductive-type input suppl\$3 source input terminal display data transmission MISFET output terminal distance "200" ". mu.m" output\$3).clm.	US-PGPUB	AND	ON	2006/11/30 19:30
S15 8	1	(current driv\$3 semiconductor MISFET reference source flow transmitt\$3 distribution current mirror second-conductive-type input suppl\$3 source input terminal display data transmission MISFET output terminal distance output\$3). clm.	US-PGPUB	AND	ON	2006/11/30 19:31